

Silicon NPN Power Transistors

2SD1795

DESCRIPTION

- With ITO-220 package
- Switching power transistor
- DARLINGTON

PINNING

PIN	DESCRIPTION
1	Base
2	Collector
3	Emitter

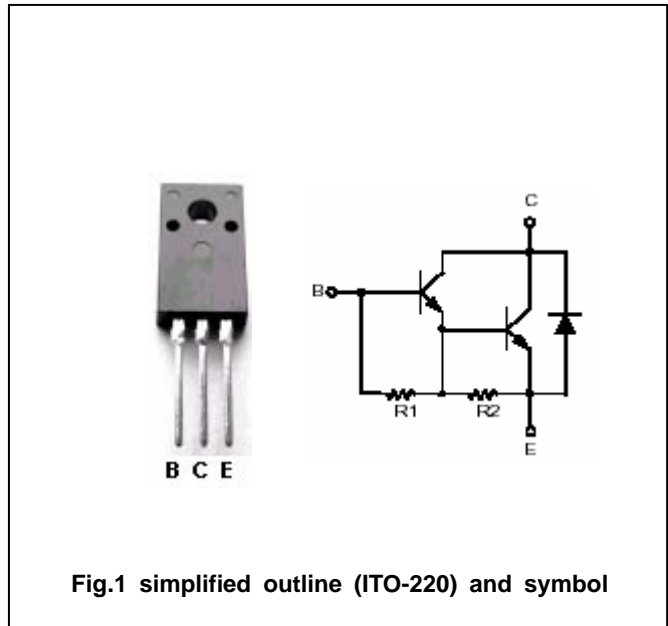


Fig.1 simplified outline (ITO-220) and symbol

Absolute maximum ratings($T_a=25^{\circ}\text{C}$)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	500	V
V_{CEO}	Collector-emitter voltage	Open base	400	V
V_{EBO}	Emitter-base voltage	Open collector	12	V
I_C	Collector current		10	A
I_{CM}	Collector current-Peak		15	A
I_B	Base current		0.5	A
I_{BM}	Base current-Peak		1.0	A
P_T	Total power dissipation	$T_C=25^{\circ}\text{C}$	50	W
T_j	Junction temperature		150	$^{\circ}\text{C}$
T_{stg}	Storage temperature		-55~150	$^{\circ}\text{C}$

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
$R_{th\ j-c}$	Thermal resistance junction to case	2.5	$^{\circ}\text{C}/\text{W}$

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CHARACTERISTICS

T_j=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{CEO(SUS)}	Collector-emitter sustaining voltage	I _C =10mA; I _B =0	400			V
V _{CE(sat)}	Collector-emitter saturation voltage	I _C =7A; I _B =70mA			1.5	V
V _{BE(sat)}	Base-emitter saturation voltage	I _C =7A; I _B =70mA			2.0	V
I _{CBO}	Collector cut-off current	V _{CB} =500V; I _E =0			0.1	mA
I _{CEO}	Collector cut-off current	V _{CE} =400V; I _B =0			0.1	mA
I _{EBO}	Emitter cut-off current	V _{EB} =12V; I _C =0			100	mA
h _{FE}	DC current gain	I _C =7A; V _{CE} =2V	150			
f _T	Transition frequency	I _C =1A; V _{CE} =10V		10		MHz

Switching times

t _{on}	Turn-on time	I _C =7A; I _{B1} =I _{B2} =70mA, R _L =10Ω; V _{BB2} =4V			2.0	μs
t _s	Storage time				15	μs
t _f	Fall time				15	μs

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PACKAGE OUTLINE

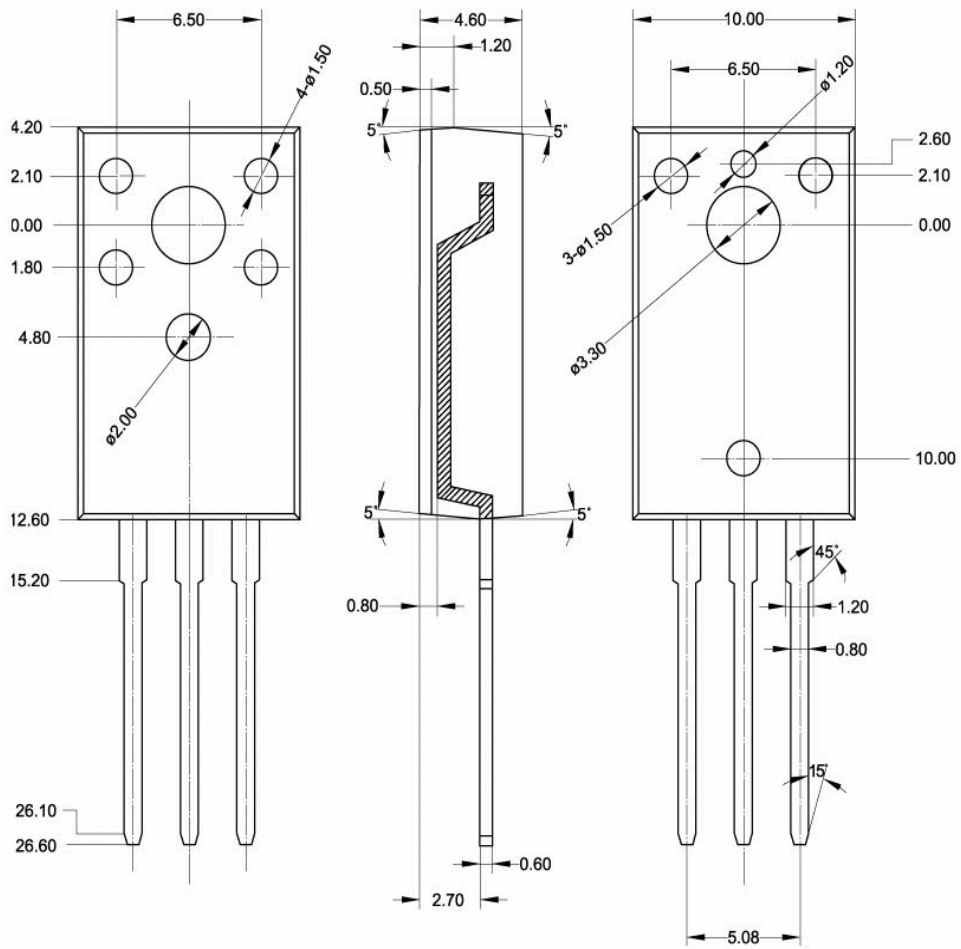


Fig.2 Outline dimensions (unindicated tolerance: ± 0.20 mm)